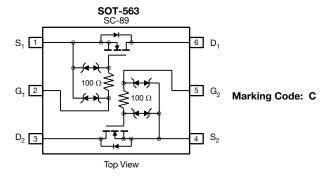
COMPLIANT HALOGEN

FREE



Dual N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (mA)		
20	0.70 at V _{GS} = 4.5 V	600		
	0.85 at V _{GS} = 2.5 V	500		
	1.25 at V _{GS} = 1.8 V	350		



Ordering Information: Si1024X-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 **Definition**
- TrenchFET® Power MOSFET: 1.8 V Rated
- Very Small Footprint
- High-Side Switching
- Low On-Resistance: 0.7 Ω
- Low Threshold: 0.8 V (typ.)
- Fast Switching Speed: 10 ns
- 1.8 V Operation
- Gate-Source ESD Protected: 2000 V
- Compliant to RoHS Directive 2002/95/EC

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- **High-Speed Circuits**
- Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- **Battery Operated Systems**
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 6		V
Out in the Position Out of the 150 000	T _A = 25 °C	I _D	515	485	^
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		370	350	
Pulsed Drain Current ^b	·	I _{DM}	650		mA
Continuous Source Current (Diode Conduction) ^a		Is	450 380		
	T _A = 25 °C	P _D	280	250	mW
Maximum Power Dissipation ^a	T _A = 85 °C		145	130	
Operating Junction and Storage Temperature Range	Junction and Storage Temperature Range T _J , T _{stg} - 55 to 150		to 150	°C	
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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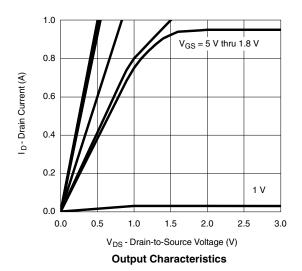
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.45		0.9	V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 0.5	± 1	μΑ	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$		0.3	100	nA	
		V_{DS} = 20 V, V_{GS} = 0 V, T_{J} = 85 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	700			mA	
Drain-Source On-State Resistance ^a		$V_{GS} = 4.5 \text{ V}, I_D = 600 \text{ mA}$		0.41	0.70	Ω	
	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 500 \text{ mA}$		0.53	0.85		
		V _{GS} = 1.8 V, I _D = 350 mA		0.70	1.25		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 400 mA		1		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 150 mA, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			750			
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 250 \text{ mA}$		75		рC	
Gate-Drain Charge	Q_{gd}			225]	
Turn-On Time	t _{d(on)}	V_{DD} = 10 V, R_L = 47 Ω		10		20	
Turn-Off Time	t _{d(off)}	$I_D \approx 200$ mA, $V_{GEN} = 4.5$ V, $R_g = 10~\Omega$		36		ns	

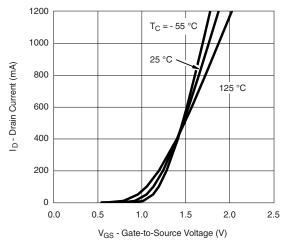
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

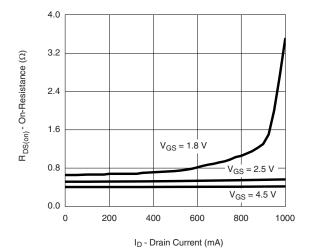




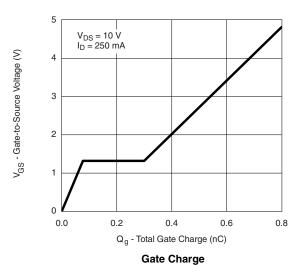


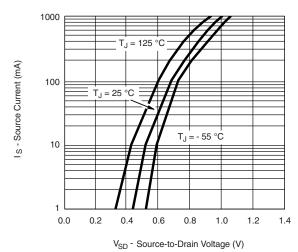


TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)

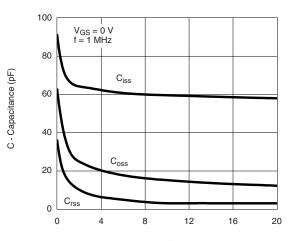


On-Resistance vs. Drain Current



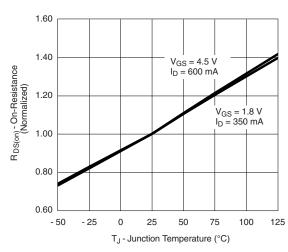


Source-Drain Diode Forward Voltage

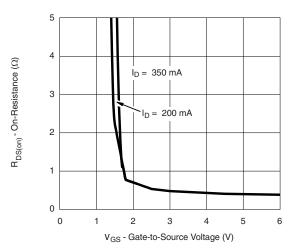


V_{DS} - Drain-to-Source Voltage (V)

Capacitance



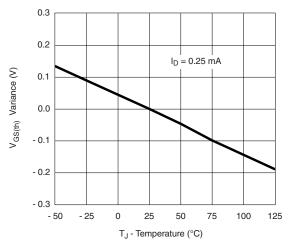
On-Resistance vs. Junction Temperature

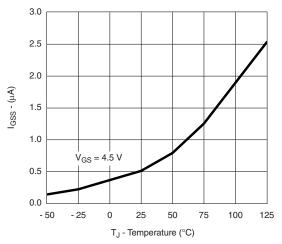


On-Resistance vs. Gate-to-Source Voltage

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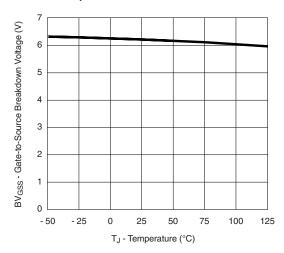
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



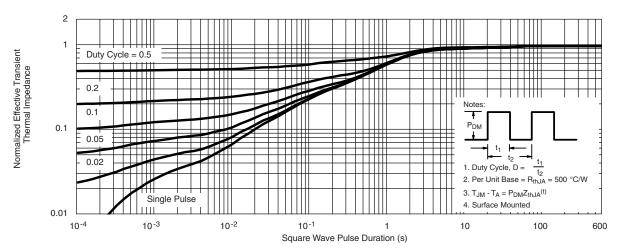


Threshold Voltage Variance vs. Temperature





BV_{GSS} vs. Temperature

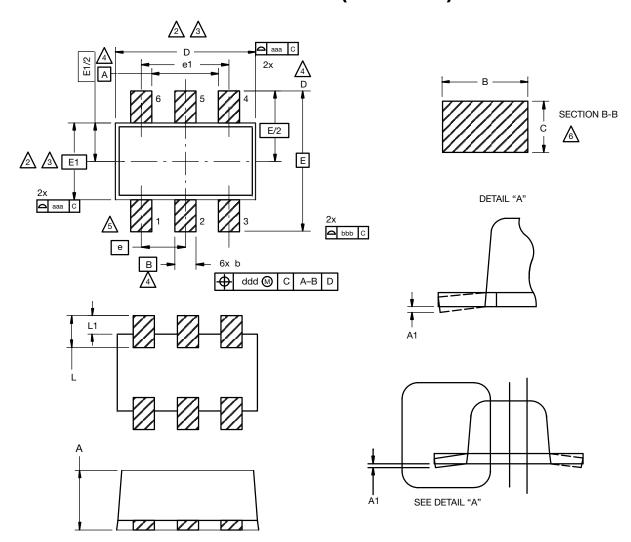


Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71170.



SC-89 6-Leads (SOT-563F)



Notes

1. Dimensions in millimeters.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

ADatums A, B and D to be determined 0.10 mm from the lead tip.

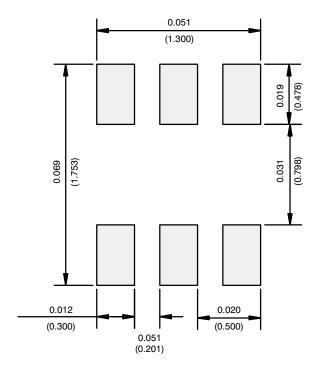
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS			
	MIN.	NOM.	MAX.	
Α	0.56	0.58	0.60	
A1	0	0.02	0.10	
b	0.15	0.22	0.30	
С	0.10	0.14	0.18	
D	1.50	1.60	1.70	
E	1.50	1.60	1.70	
E1	1.15	1.20	1.25	
е	0.45	0.50	0.55	
e1	0.95	1.00	1.05	
L	0.25	0.35	0.50	
L1	0.10	0.20	0.30	
C14-0439-Rev. C, 11-Aug-14 DWG: 5880				



RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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